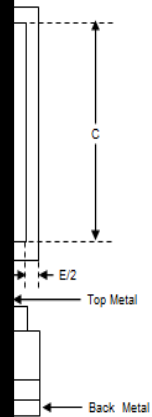


S(A)S-255A

Schottky barrier diode with tre MOS structure

Item		Information	
	Die Size (A)	2	94 mil
	Top Metal Pad Size (B)	2	90mil
	Chip Size (C)	2	91mil
	Wafer Thickness (D)	2	9.5 mil
	Scribe Line Width (E)		3.15 mil
	Wafer Size		6 inch
	Top Side Metallization		AL/Ag
	Back Side Metallization		Ni Ag
	Recommended Storage Environment	Store in original container, in dry n (6 months at an ambient temperature of 23	

stics (T_J=25

Description	Min.	Typ.	Ma	Test Condition
akdown Voltage	155	170	-	I _R =100μA
s Forward Voltage	-	0.8	0.8	I _F =10A ⁽³⁾
kage Current	-	0.5	10	V _R =150V
d Storage Temperature	-40	to 150	Max	